VARO SEMICONDUCTOR, INC., P.O. Box 469013
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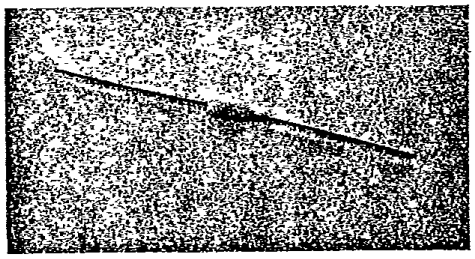
DLS 131

High Voltage Rectifier H 1746 Series

January 1984

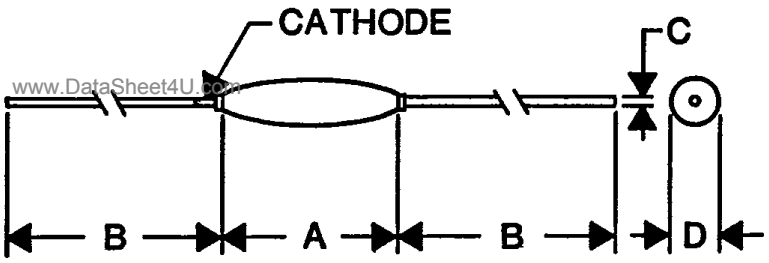
- **Glass Passivated**
- **Glass Encapsulated**
- **Platinum Doped**
- **Aluminum Bonded**
- **Uniform Chip-To-Chip Recovery**



MAXIMUM RATINGS (At T_A = 25°C unless otherwise noted)	SYMBOL	-25	-24	-23	-22	-21	UNITS
Repetitive Peak Reverse Voltage*	V_{RRM}	25	24	23	22	21	kV
Forward Current, Repetitive Peak	I_{FRM}	100					mA
Forward Current (Total RMS)	$I_{F(RMS)}$	10					mA
Average Rectified Forward Current, 15.75 kHz, 15% duty cycle, capacitive load	$I_{F(AV)}$	1.5					mA
Operating Junction Temperature	T_J	-40 to +110					°C
Operating Case Temperature	T_C	-40 to +100					°C
Storage Temperature	T_{STG}	-40 to +150					°C

ELECTRICAL CHARACTERISTICS (At T_A = 25°C unless otherwise noted)	SYMBOL		UNITS
Max. Forward Voltage, @ I_F = 5 mA	V_F	70	V
Max. Reverse Current, @ V_R = Rated V_{RRM}*	I_R	2	µA
Max. Reverse Recovery Time (Circuit Fig. 2)	t_{rr}	175 max. 100 typical	ns
Max. Junction Capacitance, f = 100 kHz, V_R = 100 VDC	C_J	0.4	pF
Soldering Temperature = 260°C Max. for 10 sec. Max., 0.125 inch min. from glass			

*For reverse voltage testing, the rectifier must be in a suitable dielectric such as oil, pressurized nitrogen, epoxy, or Fluorinert FC 43.



NOMINAL DIMENSIONS		
LTR	INCHES	MILLIMETERS
A	.460 ± .030	11,68 ± 0,76
B	1.19 ± .03	30,23 ± 0,76
C	.0236 ± .0015	0,6 ± 0,04
D	.135 MAX.	3,43 MAX.

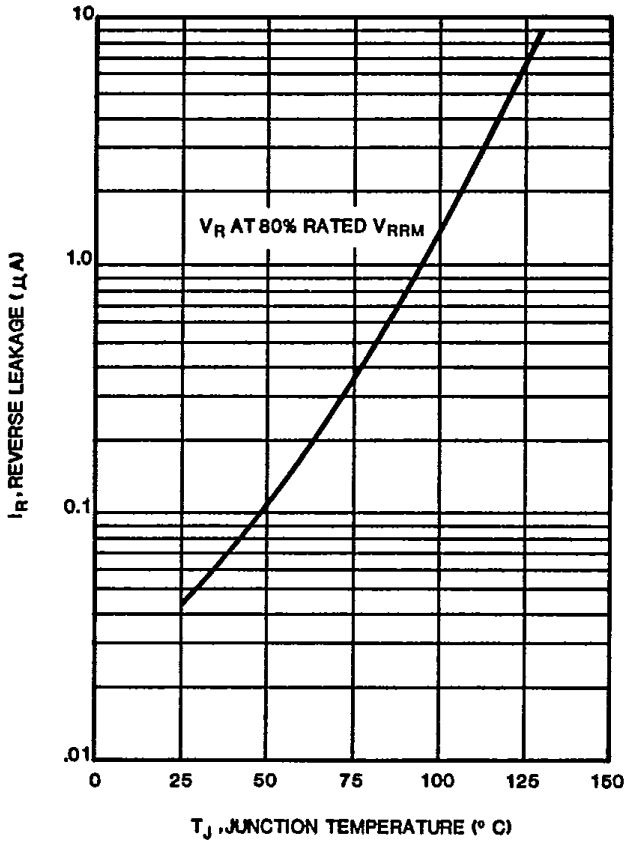


FIG. 1

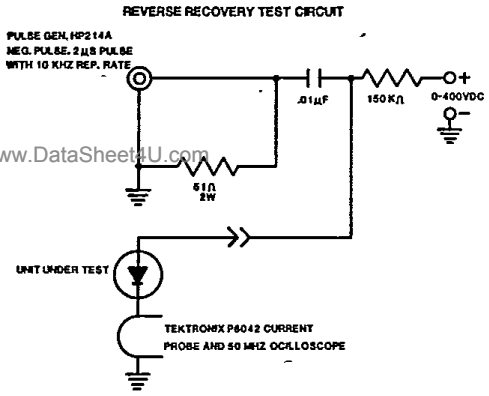


FIG. 2A

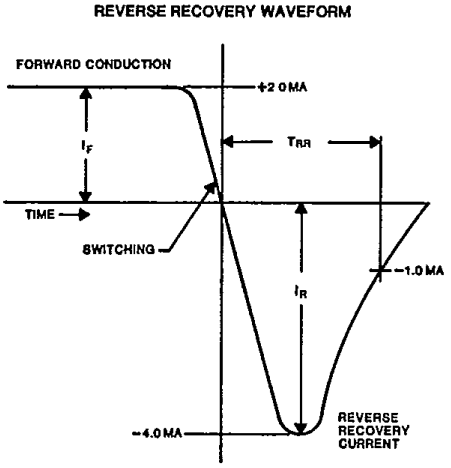


FIG. 2B

